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DATA SHEET

PART NO. : L-314EIR1BC

REV : A / 1

CUSTOMER'S APPROVAL : _____

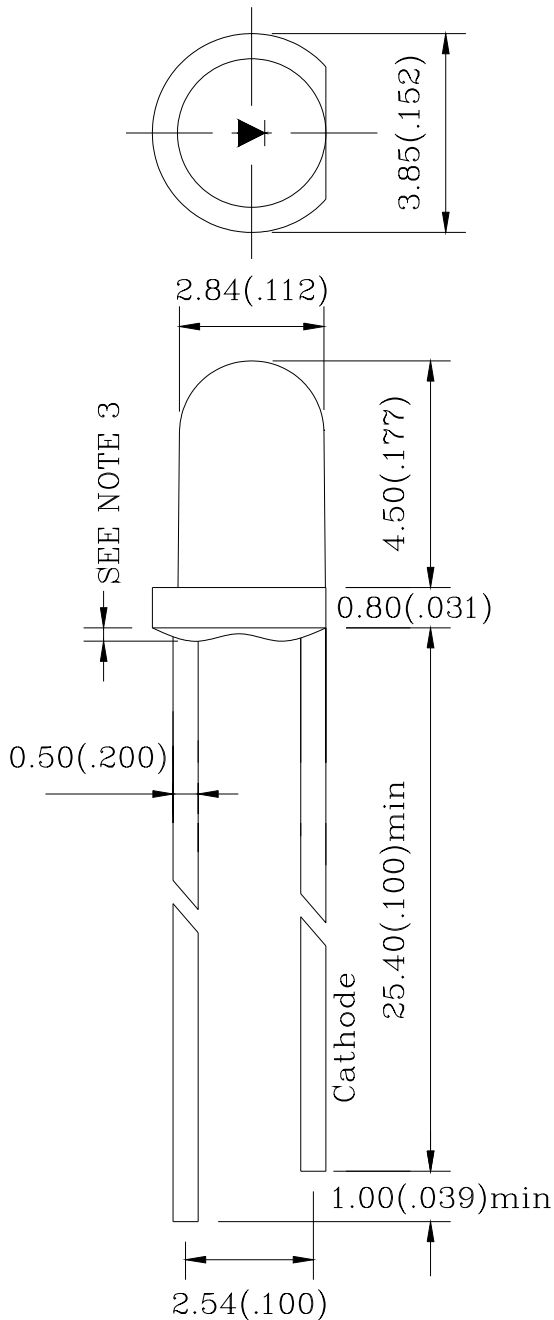
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PACKAGE DIMENSIONS



Note:

1. All Dimensions are in millimeters.
2. Tolerance is $\pm 0.25\text{mm}$ (0.010 ") Unless otherwise specified.
3. Protruded resin under flange is 1.5mm (0.059 ") max.
4. Lead spacing is measured where the leads emerge from the package.
5. Specification are subject to change without notice



3.0 mm INFRARED EMITTING DIODE

L-314EIR1BC

REV:A / 1

FEATURES

- * EXTRA HIGH RADIANT POWER AND RADIANT INTENSITY
- * LOW FORWARD VOLTAGE
- * SUITABLE FOR HIGH PULSE CURRENT OPERATION INTENSITY
- * HIGH RELIABILITY

CHIP MATERIALS

- * Dice Material : GaAlAs/GaAs
- * Lens Color :BLUE TRANSPARENT

ABSOLUTE MAXIMUM RATING : (Ta = 25°C)

SYMBOL	PARAMETER	MAX	UNIT
PAD	Power Dissipation	180	mW
VR	Reverse Voltage	5	V
IF	Forward Current	100	mA
IPF	Peak forward current (F=1KHZ,duty=0.1)	400	mA
Topr	Operating Temperature Range	-35°C to 85°C	
Tstg	Storage Temperature Range	-35°C to 85°C	

Lead Soldering Temperature { 1.6mm(0.063 inch) From Body } 260°C ± 5°C for 5 Seconds

ELECTRO-OPTICAL CHARACTERISTICS : (Ta = 25°C)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
VF	Forward Voltage	IF = 20mA IF = 100mA		1.3 1.5	1.8	V
IR	Reverse Current	VR = 5V			10	μA
λp	Peak Emission Wavelength	IF = 20mA		940		nm
2θ1/2	Half Intensity Angle	IF = 20mA		20		deg
IE	Radiant Intensity	IF = 20mA IF=100mA		6 30		mw/sr

